Wei-Jun Fan

List of Publications by Year
in descending order

217 papers	3,735 citations	236612 25 h-index	161609 54 g-index
218 all docs	218 docs citations	218 times ranked	3420 citing authors

#	Article	IF	Citations
1	Polarityâ€Switchable and Selfâ€Driven Photoâ€Response Based on Vertically Stacked Typeâ€II GeSe/SnS₂ Heterojunction. Advanced Materials Interfaces, 2022, 9, .	1.9	18
2	Transferable single-layer GeSn nanomembrane resonant-cavity-enhanced photodetectors for 2 Î¼m band optical communication and multi-spectral short-wave infrared sensing. Nanoscale, 2022, 14, 7341-7349.	2.8	7
3	Direct bandgap GeSn nanowires enabled with ultrahigh tension from harnessing intrinsic compressive strain. Applied Physics Letters, 2022, 120, .	1.5	1
4	Study of Complex Optical Constants of Neat Cadmium Selenide Nanoplatelets Thin Films by Spectroscopic Ellipsometry. Journal of Physical Chemistry Letters, 2021, 12, 191-198.	2.1	17
5	Simulation of high-efficiency resonant-cavity-enhanced GeSn single-photon avalanche photodiodes for sensing and optical quantum applications. IEEE Sensors Journal, 2021, , 1-1.	2.4	11
6	Ge_{0.95}Sn_{0.05} Gate-All-Around p-Channel Metal-Oxide-Semiconductor Field-Effect Transistors with Sub-3 nm Nanowire Width. Nano Letters, 2021, 21, 5555-5563.	4.5	21
7	Employing Equivalent Circuit Models to Study the Performance of Seleniumâ€Based Solar Cells with Polymers as Hole Transport Layers. Small, 2021, 17, e2101226.	5.2	7
8	GeSn-on-insulator dual-waveband resonant-cavity-enhanced photodetectors at the 2â€‰â€‰Âµm and 1.55â€‰â€‰Âµm optical communication bands. Optics Letters, 2021, 46, 3809.	1.7	8
9	Nearly total optical transmission of linearly polarized light through transparent electrode composed of GaSb monolithic high-contrast grating integrated with gold. Nanophotonics, 2021, 10, 3823-3830.	2.9	4
10	Surface Depletion Effects in Bromide-Ligated Colloidal Cadmium Selenide Nanoplatelets: Toward Efficient Emission at High Temperature. Journal of Physical Chemistry Letters, 2021, 12, 9086-9093.	2.1	9
11	Effect of thickness on the electronic structure and optical properties of quasi two-dimensional perovskite CsPbBr3 nanoplatelets. Journal of Luminescence, 2021, 239, 118392.	1.5	5
12	Vertically stacked Bi₂Se₃/MoTe₂ heterostructure with large band offsets for nanoelectronics. Nanoscale, 2021, 13, 15403-15414.	2.8	23
13	Hybridized surface lattice modes in intercalated 3-disk plasmonic crystals for high figure-of-merit plasmonic sensing. Nanoscale, 2021, 13, 4092-4102.	2.8	9
14	Anti-ambipolar behavior and photovoltaic effect in p-MoTe₂/n-InSe heterojunctions. Journal of Materials Chemistry C, 2021, 9, 10372-10380.	2.7	24
15	Improving the hole transport performance of perovskite solar cells through adjusting the mobility of the as-synthesized conjugated polymer. Journal of Materials Chemistry C, 2021, 9, 3421-3428.	2.7	12
16	Realizing White Emission of Single-Layer Dual-Color Perovskite Light-Emitting Devices by Modulating the Electroluminescence Emission Spectra. Journal of Physical Chemistry Letters, 2021, 12, 10197-10203.	2.1	16
17	Suspended germanium membranes photodetector with tunable biaxial tensile strain and location-determined wavelength-selective photoresponsivity. Applied Physics Letters, 2021, 119, .	1.5	6
18	Effect of Size on the Electronic Structure and Optical Properties of Cubic CsPbBr₃ Quantum Dots. IEEE Journal of Quantum Electronics, 2020, 56, 1-7.	1.0	3

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19	The theoretical direct-band-gap optical gain of Germanium nanowires. Scientific Reports, 2020, 10, 32.	1.6	6
20	GeSn/GaAs Hetero-Structure by Magnetron Sputtering. IEEE Journal of Quantum Electronics, 2020, 56, 1-5.	1.0	1
21	Molecular Aggregation of Naphthalene Diimide(NDI) Derivatives in Electron Transport Layers of Inverted Perovskite Solar Cells and Their Influence on the Device Performance. Chemistry - an Asian Journal, 2020, 15, 112-121.	1.7	20
22	Growth of Direct Bandgap Ge1âˆ'xSnx Alloys by Modified Magnetron Sputtering. IEEE Journal of Quantum Electronics, 2020, 56, 1-4.	1.0	0
23	Chip-Based Measurement-Device-Independent Quantum Key Distribution Using Integrated Silicon Photonic Systems. Physical Review Applied, 2020, 14, .	1.5	32
24	Inverted Solar Cells with Thermally Evaporated Selenium as an Active Layer. ACS Applied Energy Materials, 2020, 3, 7345-7352.	2.5	13
25	Seleniumâ€Based Solar Cell with Conjugated Polymers as Both Electron and Hole Transport Layers to Realize High Water Tolerance as well as Good Longâ€Term and Thermal Stability. Solar Rrl, 2020, 4, 2000425.	3.1	3
26	Improving the Fill Factor of Perovskite Solar Cells by Employing an Amine-tethered Diketopyrrolopyrrole-Based Polymer as the Dopant-free Hole Transport Layer. ACS Applied Energy Materials, 2020, 3, 9600-9609.	2.5	26
27	Band Structure of Strained $mathrm{Ge}_{1-x}~mathrm{Sn}_{x}$ Alloy: A Full-Zone 30-Band ${k}cdot{p}$ Model. IEEE Journal of Quantum Electronics, 2020, 56, 1-8.	1.0	4
28	Improved stability and efficiency of polymer-based selenium solar cells through the usage of tin(<scp>iv</scp>) oxide in the electron transport layers and the analysis of aging dynamics. Physical Chemistry Chemical Physics, 2020, 22, 14838-14845.	1.3	7
29	Optical properties of two-dimensional semi-conductive MXene Sc2CO produced by sputtering. Optik, 2020, 219, 165046.	1.4	13
30	The Theoretical Optical Gain of Ge 1âˆ' x Sn x Nanowires. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900704.	1.2	3
31	Virtual Special Issue Dedicated to the 10th International Conference on Materials for Advanced Technologies (ICMAT), Symposium C: Semiconductor Photonics. IEEE Journal of Quantum Electronics, 2020, 56, 1-3.	1.0	0
32	Strong Plasmon-Wannier Mott Exciton Interaction with High Aspect Ratio Colloidal Quantum Wells. Matter, 2020, 2, 1550-1563.	5.0	18
33	Theoretical design of mid-infrared interband cascade lasers in SiGeSn system. New Journal of Physics, 2020, 22, 083061.	1.2	4
34	Comparative study of U- and U4-split-ring resonator-based metasurfaces for sensing in near- and mid-infrared region. Journal of Optics (United Kingdom), 2020, 22, 125104.	1.0	1
35	Ultrathin Highly Luminescent Twoâ€Monolayer Colloidal CdSe Nanoplatelets. Advanced Functional Materials, 2019, 29, 1901028.	7.8	56
36	Band structure of Ge_{1âˆ'x}Sn_x alloy: a full-zone 30-band k Â· p model. New Journal of Physics, 2019, 21, 073037.	1.2	24

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37	Optical haze of randomly arranged silver nanowire transparent conductive films with wide range of nanowire diameters. AIP Advances, 2018, 8, 035201.	0.6	10
38	Highly Efficient Ultrathin Plasmonic Insulator-Metal-Insulator-Metal Solar Cell. Plasmonics, 2018, 13, 141-145.	1.8	6
39	Effect of size and shape on electronic and optical properties of CdSe quantum dots. Optik, 2018, 155, 242-250.	1.4	18
40	Introducing Cations (Zn²⁺, Sn²⁺ and Mg²⁺) and Anions(Cl^{â^’}) to Tune Mn Photoluminescence Intensity of Doped Perovskite Nanocrystals(CsPbCl₃). ChemistrySelect, 2018, 3, 11986-11992.	0.7	7
41	Bulk inversion asymmetry effect on band structure and optical transition of a new class all-inorganic cubic perovskite nanoplatelet. AIP Advances, 2018, 8, .	0.6	3
42	Towards theoretical analysis of optoelectronic performance of uniform and random metallic nanowire layers. Thin Solid Films, 2017, 626, 140-144.	0.8	4
43	Temperature-dependent optoelectronic properties of quasi-2D colloidal cadmium selenide nanoplatelets. Nanoscale, 2017, 9, 6595-6605.	2.8	18
44	Solution-processed inorganic copper(i) thiocyanate as a hole injection layer for high-performance quantum dot-based light-emitting diodes. RSC Advances, 2017, 7, 26322-26327.	1.7	27
45	Optoelectronics of inverted type-I CdS/CdSe core/crown quantum ring. Journal of Applied Physics, 2017, 122, 163102.	1.1	0
46	Quantum spin Hall effect and topological phase transition in InNxBiySb1â^’xâ^’y/InSb quantum wells. New Journal of Physics, 2017, 19, 073031.	1.2	11
47	Strain profile and size dependent electronic bandstructure of Type-I CdS/CdSe quantum ring. , 2017, , .		0
48	Theoretical investigations of excitonic absorption in quasi two-dimensional CdSe nanoplatelets. , 2017, , .		2
49	KdotPsoft: Modelling and Simulation of Semiconductors and Device Physics. Procedia Engineering, 2017, 215, 36-40.	1.2	0
50	Theoretical Model of Ge x Sn 1-x /Ge Quantum Well with Build-in Compressive Strain. Procedia Engineering, 2017, 215, 77-81.	1.2	1
51	Electronic Structure and Optical Gain of InNBiAs/InP Pyramidal Quantum Dots. Procedia Engineering, 2017, 215, 31-35.	1.2	0
52	Temperature enhanced spontaneous emission rate spectra in GeSn/Ge quantum wells. Optical Materials Express, 2017, 7, 800.	1.6	9
53	Effect of silver nanowire length in a broad range on optical and electrical properties as a transparent conductive film. Optical Materials Express, 2017, 7, 1105.	1.6	26
54	Inverted Type-I CdS/CdSe Core/Crown colloidal quantum ring. , 2017, , .		1

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55	Towards understanding the difference of optoelectronic performance between micro- and nanoscale metallic layers. Optical Materials Express, 2016, 6, 2655.	1.6	4
56	Effect of lateral size and thickness on the electronic structure and optical properties of quasi two-dimensional CdSe and CdS nanoplatelets. Journal of Applied Physics, 2016, 119, .	1.1	28
57	Electronic bandstructure and optical gain of lattice matched III-V dilute nitride bismide quantum wells for 1.55â€‰<i>Î¼</i>m optical communication systems. Journal of Applied Physics, 2016, 120, .	1.1	10
58	Electronic band structure and optical gain of GaNxBiyAs1âˆ'xâˆ'y/GaAs pyramidal quantum dots. Journal of Applied Physics, 2016, 119, 143103.	1.1	13
59	Design, Simulations, and Optimizations of Mid-infrared Multiple Quantum Well LEDs. Procedia Engineering, 2016, 140, 36-42.	1.2	7
60	Transparent conductive nanoporous aluminium mesh prepared by electrochemical anodizing. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2174-2178.	0.8	11
61	Comparative analysis of opto-electronic performance of aluminium and silver nano-porous and nano-wired layers. Optics Express, 2015, 23, 26794.	1.7	10
62	Optoelectronic performance optimization for transparent conductive layers based on randomly arranged silver nanorods. Optics Express, 2015, 23, 6209.	1.7	24
63	Theoretical comparison of optical and electronic properties of uniformly and randomly arranged nano-porous ultra-thin layers. Optics Express, 2015, 23, 17860.	1.7	11
64	Strain Profile and Size Dependent Electronic Band Structure of GeSn/SiSn Quantum Dots for Optoelectronic Application. , 2014, , .		1
65	OPTICAL GAIN AND ENERGY BAND STRUCTURE OF PHOTONIC CRYSTAL VCSELs WITH HIGH-INDEX-CONTRAST SUBWAVELENGTH GRATINGS. Journal of Molecular and Engineering Materials, 2014, 02, 1440014.	0.9	0
66	Strain profile, electronic band structure and optical gain of self-assembled Ge quantum dots on SiGe virtual substrate. , 2014, , .		0
67	Electronic structure of Ge/Si<inf>x</inf>Sn<inf>y</inf>Ge<inf>1−x−y</inf> quantum dots. , 2013, , .		1
68	Current Conduction Model for Oxide-Based Resistive Random Access Memory Verified by Low-Frequency Noise Analysis. IEEE Transactions on Electron Devices, 2013, 60, 1272-1275.	1.6	20
69	Orientation dependence of electronic structure and optical gain of (11N)-oriented III-V-N quantum wells. Journal of Applied Physics, 2013, 113, 083102.	1.1	8
70	Tensile-strain and doping enhanced direct bandgap optical transition of n+ doped Ge/GeSi quantum wells. Journal of Applied Physics, 2013, 114, .	1.1	19
71	Electronic band structure and effective mass parameters of Ge1-xSnx alloys. Journal of Applied Physics, 2012, 112, .	1.1	194
72	Band structures and optical gain of InGaAsN/GaAsN strained quantum wells under electric field. , 2012, , .		0

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73	Shape effects on the electronic structure and the optical gain of InAsN/GaAs nanostructures: From a quantum lens to a quantum ring. Superlattices and Microstructures, 2012, 52, 618-631.	1.4	4
74	1.3-mum In(Ga)As Quantum-Dot VCSELs Fabricated by Dielectric-Free Approach With Surface-Relief Process. IEEE Photonics Technology Letters, 2011, 23, 91-93.	1.3	5
75	Nanostructure model and optical properties of InAs/GaAs quantum dot in vertical cavity surface emitting lasers. Opto-electronics Review, 2011, 19, .	2.4	2
76	Electronic structure and optical gain of InAsPN/GaP(N) quantum dots. Superlattices and Microstructures, 2011, 49, 1-8.	1.4	3
77	Band structures and optical gain of strained GaAsxP1â^'xâ^'yNy/GaP quantum wells. Applied Physics Letters, 2011, 98, 121112.	1.5	7
78	Low threshold current density, low resistance oxide-confined VCSEL fabricated by a dielectric-free approach. Applied Physics B: Lasers and Optics, 2010, 98, 773-778.	1.1	8
79	Microphotoluminescence investigation of InAs quantum dot active region in 1.3â€‚Î¼m vertical cavity surface emitting laser structure. Journal of Applied Physics, 2010, 108, 073111.	1.1	6
80	Electronic structure and optical gain of InAsSbN/InAs quantum dots. Computational Materials Science, 2010, 49, S10-S14.	1.4	1
81	The natural valence band offset of dilute GaAs1â^'xNx and GaAs: The first-principles approach. Computational Materials Science, 2010, 49, S150-S152.	1.4	1
82	Self-heating effect in 1.3â€‚Î¼m p-doped InAs/GaAs quantum dot vertical cavity surface emitting lasers. Journal of Applied Physics, 2010, 107, 063107.	1.1	3
83	Theoretical gain of strained GeSn0.02/Ge1â^'xâ^'yâ€²SixSnyâ€² quantum well laser. Journal of Applied Physics, 2010, 107, 073108.	1.1	39
84	Band structures and optical gain of direct-bandgap tensile strained Ge/Ge<inf>1-X-Y</inf>Si<inf>X</inf>Sn<inf>Y</inf> type I quantum wells. , 2010, , .		1
85	Fabrication and Characterization of 1.3-Âµm InAs Quantum-Dot VCSELs and Monolithic VCSEL Arrays. , 2009, , .		0
86	Room-temperature continuous-wave operation of the In(Ga)As/GaAs quantum-dot VCSELs for the 1.3 Âµm optical-fibre communication. Semiconductor Science and Technology, 2009, 24, 055003.	1.0	22
87	Temperature Characteristics of 1.3-mum p-Doped InAsâ€"GaAs Quantum-Dot Vertical-Cavity Surface-Emitting Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 743-748.	1.9	14
88	Electronic structure and optical gain of truncated InAs1â^'xNx /GaAs quantum dots. Superlattices and Microstructures, 2009, 46, 498-506.	1.4	4
89	Electronic structure and optical gain saturation of InAs1â^'xNx/GaAs quantum dots. Journal of Applied Physics, 2009, 105, 123705.	1.1	16
90	High-Temperature Continuous-Wave Single-Mode Operation of 1.3-mum p-Doped InAsâ€"GaAs Quantum-Dot VCSELs. IEEE Photonics Technology Letters, 2009, 21, 1211-1213.	1.3	29

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91	Investigation of high-speed modulaiton of 1.3μm InAs/InGaAs quantum dot VCSELs. , 2009, , .		1
92	Fabrication and modulation characteristics of 1.3â€‰Âµm p-doped InAs quantum dot vertical cavity surface emitting lasers. Journal Physics D: Applied Physics, 2009, 42, 085117.	1.3	8
93	Band Structure and Optical Gain of 1.3 um GaAsSbN/GaAs Compressively Strained Quantum Well Laser. Advanced Materials Research, 2008, 31, 95-97.	0.3	0
94	Pseudo-potential band structure calculation of InSb ultra-thin films and its application to assess the n-metal-oxide-semiconductor transistor performance. Semiconductor Science and Technology, 2008, 23, 025009.	1.0	6
95	Analysis and Design of Antiresonant Reflecting Optical Waveguide Vertical-Cavity Surface-Emitting Lasers for Above-Threshold Operation. Journal of Lightwave Technology, 2008, 26, 1935-1942.	2.7	1
96	Electronic structures of wurtzite ZnO, BeO, MgO and p-type doping in Zn1â^{ˆ'}xYxO (Y=Mg, Be). Computational Materials Science, 2008, 44, 72-78.	1.4	25
97	Design of Stable Single-Mode Chaotic Light Source Using Antiresonant Reflecting Optical Waveguide Vertical-Cavity Surface-Emitting Lasers. IEEE Journal of Quantum Electronics, 2008, 44, 338-345.	1.0	1
98	Investigation of Temperature Characteristics for 1.3-Â¿m InAs Quantum Dot VCSELs with Planar Electrodes Configuration. , 2008, , .		0
99	Influence of Oxide Aperture on the Properties of 1.3Â¿m InAs-GaAs Quantum-Dot VCSELs. , 2008, , .		3
100	Complicated effects of nitrogen on the structural and optical properties of InAs(N)/GaAs quantum dots. , 2008, , .		0
101	Rashba spin splitting of the minibands of coupled InAsâˆ•GaAs pyramid quantum dots. Applied Physics Letters, 2008, 92, .	1.5	5
102	Intersubband transitions in InGaAsN/GaAs quantum wells. Journal of Applied Physics, 2008, 104, 053119.	1.1	6
103	Dilute nitride based double-barrier quantum wells for intersubband absorption at 1.31 and<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>1.55</mml:mn><mml:mtext>â€‚</mml:mtext><mml:mi>Î¼</mml:mi><mml:mtext>m</mml:m Physical Review B, 2008, 77, .	1.1	5
104	Room-temperature highly anisotropic ferromagnetism and uniaxial spin amplification in (In,Mn)As quantum dots. Applied Physics Letters, 2008, 92, 013129.	1.5	4
105	1.3-Î¼m InAs quantum dot vertical cavity surface emitting lasers with planar electrode configuration. Proceedings of SPIE, 2008, , .	0.8	1
106	Design of InxGa1âˆ'xAs1âˆ'yNyâˆ•AlAs quantum cascade structures for 3.4Î¼m intersubband emission. Journal of Applied Physics, 2007, 101, 084504.	1.1	0
107	High and electric field tunable Curie temperature in diluted magnetic semiconductor nanowires and nanoslabs. Applied Physics Letters, 2007, 90, 253110.	1.5	10
108	Influence ofNdoping on the Rashba coefficient, semiconductor-metal transition, and electron effective mass inInSb1âˆ'xNxnanowires: Ten-bandkâˆ™pmodel. Physical Review B, 2007, 75, .	1.1	13

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109	Electric field tunable electron g factor and high asymmetrical Stark effect in InAs1â^'xNx quantum dots. Applied Physics Letters, 2007, 90, 153103.	1.5	5
110	Highly anisotropic and electric field tunable Zeeman splittings in Mn-doped CdS nanowires. Physical Review B, 2007, 76, .	1.1	4
111	GaInNAs double-barrier quantum well infrared photodetector with the photodetection at 1.24Î¼m. Applied Physics Letters, 2007, 91, .	1.5	8
112	Interdiffusion in narrow InGaAsNâ^•GaAs quantum wells. Journal of Applied Physics, 2007, 101, 103111.	1.1	3
113	Theoretical study of quantum well infrared photodetectors with asymmetric well and barrier structures for broadband photodetection. Journal of Applied Physics, 2007, 101, 033114.	1.1	10
114	Anisotropic Zeeman splitting and Stark shift of In1â^'yMnyAs1â^'xNx oblate quantum dots. Journal of Applied Physics, 2007, 102, .	1.1	1
115	Hole-mediated electric field tunable high Curie temperature in Mn-doped wurtzite ZnO nanowires. Applied Physics Letters, 2007, 91, .	1.5	1
116	Giant and zero electron g factors of dilute nitride semiconductor nanowires. Applied Physics Letters, 2007, 90, 193111.	1.5	10
117	Highly anisotropic Zeeman splittings of wurtzite Cd1â^'xMnxSe quantum dots. Applied Physics Letters, 2007, 91, 113108.	1.5	6
118	Improvement of GaInNAs pâ€iâ€n photodetector responsivity by antimony incorporation. Journal of Applied Physics, 2007, 101, 033122.	1.1	10
119	Annealing effects on the optical properties of a GaInNAs double barrier quantum well infrared photodetector. Applied Physics Letters, 2007, 91, 041905.	1.5	2
120	Investigation of Intersubband Transition in GaAs/AlGaAs Quantum Well Infrared Photodetectors. Advanced Materials Research, 2007, 31, 105-107.	0.3	1
121	Band structure investigation of strained Si1-xGex/Si coupled quantum wells. International Journal of Nanotechnology, 2007, 4, 431.	0.1	0
122	High Areal Density and Broadband Emission from InAs Quantum Dots for Superluminescent Diodes. , 2007, , .		0
123	Origins of high radiative efficiency and wideband emission from InAs quantum dots. Applied Physics Letters, 2007, 91, .	1.5	8
124	Tuning InAs quantum dots for high areal density and wideband emission. Applied Physics Letters, 2007, 90, 113103.	1.5	26
125	Characterizations of a GaInNAs double-barrier quantum-well infrared photo-detector with the near-infrared photo-detection. , 2007, , .		0
126	1.31Â µm GaAs-based heterojunction pâ€"iâ€"n photodetectors using InGaAsNSb as the intrinsic layer grown by molecular beam epitaxy. Thin Solid Films, 2007, 515, 4441-4444.	0.8	2

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127	Normal incidence silicon doped p-type GaAs/AlGaAs quantum-well infrared photodetector on (111)A substrate. Infrared Physics and Technology, 2007, 50, 119-123.	1.3	7
128	Effects of size and shape on electronic states of quantum dots. Optical and Quantum Electronics, 2007, 38, 981-991.	1.5	3
129	Modeling of intersubband transitions in quantum well infrared photodetectors with complex potential profiles. Optical and Quantum Electronics, 2007, 38, 1101-1106.	1.5	0
130	Interwell coupling effect in Si/SiGe quantum wells grown by ultra high vacuum chemical vapor deposition. Nanoscale Research Letters, 2007, 2, 149-154.	3.1	0
131	Interdiffusion effect on GaAsSbN/GaAs quantum well structure studied by 10-band kâ€¢p model. Thin Solid Films, 2007, 515, 4435-4440.	0.8	4
132	Free-Excitonic Gain in ZnO/MgxZn1-xO Strained Quantum Wells. , 2006, , .		0
133	Theoretical Investigation of Excitonic Gain in<tex>$hbox ZnO--Mg_xhbox Zn_1-xhbox O$</tex>Strained Quantum Wells. IEEE Journal of Quantum Electronics, 2006, 42, 455-463.	1.0	11
134	Ridge-width dependence on high-temperature continuous-wave operation of native oxide-confined InGaAsN triple-quantum-well lasers. IEEE Photonics Technology Letters, 2006, 18, 791-793.	1.3	11
135	Effects of size and shape on electronic states of quantum dots. Physical Review B, 2006, 74, .	1.1	99
136	Electronic structures of wurtzite ZnO and ZnO/MgZnO quantum well. Journal of Crystal Growth, 2006, 287, 28-33.	0.7	32
137	Infrared absorption and currentâ€"voltage characteristic of GaAs/AlGaAs multiple quantum wells on GaAs (111)A substrate grown by solid source molecular beam epitaxy. Journal of Crystal Growth, 2006, 288, 36-39.	0.7	2
138	Band parameters and electronic structures of wurtzite ZnO and ZnOâˆ•MgZnO quantum wells. Journal of Applied Physics, 2006, 99, 013702.	1.1	74
139	Modeling Study of InSb Thin Film For Advanced III-V MOSFET Applications. , 2006, , .		6
140	Interpretation of an anomalous peak in low-temperature photoluminescence measurements of bulk GaAs1âˆ'xNx on GaAs. Journal of Applied Physics, 2006, 99, 104908.	1.1	3
141	Different temperature and pressure behavior of band edge and N-cluster emissions inGaAs0.973Sb0.022N0.005. Physical Review B, 2006, 74, .	1.1	7
142	Analysis and optimization of the annealing mechanisms in (In)GaAsN on GaAs. Semiconductor Science and Technology, 2006, 21, 808-812.	1.0	10
143	Transverse electric dominant intersubband absorption in Si-doped GaInAsNâˆ•GaAs quantum wells. Journal of Applied Physics, 2006, 99, 043514.	1.1	19
144	Study of the interdiffusion effect on the band structures of Si1âˆ'xGexâˆ•Si quantum wells. Journal of Applied Physics, 2006, 99, 076108.	1.1	6

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145	Investigation of N incorporation in InGaAs and GaAs epilayers on GaAs using solid source molecular beam epitaxy. Journal of Crystal Growth, 2005, 275, 440-447.	0.7	7
146	Surfactant and impurity properties of antimony on GaAs and GaAs1â^'xNx on GaAs [100] by solid source molecular beam epitaxy. Thin Solid Films, 2005, 488, 56-61.	0.8	11
147	Growth dynamics and optimization of Ga(In)AsN/GaAs towards 1.3Âμm and 1.55Âμm. Applied Physics A: Materials Science and Processing, 2005, 80, 631-635.	1.1	0
148	Characterizations of InzGa1â^'z As1â^'xâ^'yN xSby P-i-N structures grown on GaAs by molecular beam epitaxy. Journal of Materials Science: Materials in Electronics, 2005, 16, 301-307.	1.1	1
149	Thermal excitation effects of photoluminescence of annealed GaInNAsâ^•GaAs quantum-well laser structures grown by plasma-assisted molecular-beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1434.	1.6	2
150	Comparison of electronic band structure and optical transparency conditions ofInxGa1â^'xAs1â^'yNyâ^•GaAsquantum wells calculated by 10-band, 8-band, and 6-bandkâ^™pmodels. Physical Review B, 2005, 72, .	1.1	64
151	Valence band structure of ultrathin silicon and germanium channels in metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2005, 98, 024504.	1.1	14
152	Influence of k - p formalisms on the band structure of In/sub x/Ga/sub 1-x/As/sub 1-y/N/sub y//GaAs quantum well. , 2005, , .		0
153	Growth of p-type GaAsâ^•AlGaAs(111) quantum well infrared photodetector using solid source molecular-beam epitaxy. Journal of Applied Physics, 2005, 98, 054905.	1.1	11
154	Study of interdiffusion in GaAsSbNâ^•GaAs quantum well structure by ten-band kâ^™p method. Journal of Applied Physics, 2005, 98, 026102.	1.1	22
155	Low threshold current density and high characteristic temperature narrow-stripe native oxide-confined 1.3-Î¼m InGaAsN triple quantum well lasers. Optics Express, 2005, 13, 9045.	1.7	3
156	GaAs-based heterojunction p-i-n photodetectors using pentanary InGaAsNSb as the intrinsic layer. IEEE Photonics Technology Letters, 2005, 17, 1932-1934.	1.3	16
157	Blueshift of optical band gap in ZnO thin films grown by metal-organic chemical-vapor deposition. Journal of Applied Physics, 2005, 98, 013505.	1.1	638
158	Study of interdiffusion in GaInNAsâ^•GaAs quantum well structure emitting at 1.3Î¼m by eight-band kâ^™p method. Journal of Applied Physics, 2005, 97, 103718.	1.1	23
159	Investigation of the optical properties of InGaAsNâ^•GaAsâ^•GaAsP multiple-quantum-well laser with 8-band and 10-band kÂ·p model. Journal of Applied Physics, 2004, 96, 4663-4665.	1.1	13
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